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DL5711
DL6263

Features

- For general purpose applications
- These diodes are also available in the DO-35 case with type designation 1N5711 and 1N6263, in the Micro-MELF case with type designation MCL5711 and MCL6263.

Maximum Ratings

Repetitive Peak Reverse Voltage	DL5711 DL6263	V_R	70V 60V	
Maximum Forward Surge Current		I_{FSM}	2.0A	$t_p < 10\mu s$, $T_A = 25^\circ C$
Power Dissipation		P_{TOT}	400mW*	
Junction Temperature		T_J	125°C	
Storage Temperature Range		T_{STG}	-55~+150°C	

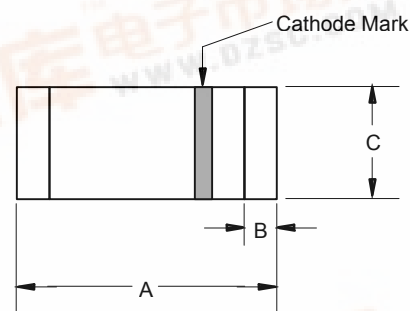
* Valid provided that electrodes are kept at ambient temperature

Electrical Characteristics @ 25°C Unless Otherwise Specified

Maximum Forward Voltage		V_F	0.41V 1.0V	$I_F = 1.0mA$ $I_F = 15mA$
Minimum Reverse Breakdown voltage	DL5711 DL6263	V_R	70V 60V	
Maximum Leakage current		I_R	200nA	$V_R = 50V$
Maximum Junction Capacitance		C_J	2.0pF	$V_R = 0$, $f = 1MHz$
Maximum Reverse recovery time		t_{rr}	1.0ns	$I_F = 5.0mA$, $I_R = 5.0mA$
Maximum Thermal resistance junction to Ambient Air		$R_{\theta JA}$	0.3K/ W	

Small Signal Schottky Diodes

MINIMELF



DIMENSION					
DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	.134	.142	3.40	3.60	
B	.008	.016	0.20	0.40	
C	.055	.059	1.40	1.50	

SUGGESTED SOLDER PAD LAYOUT

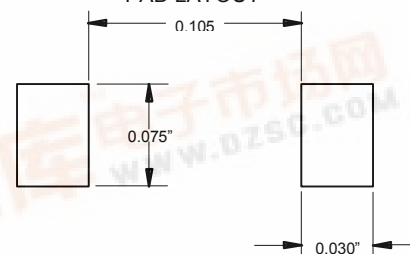


Fig.1 Typical variation of fwd. current vs forward. voltage for primary conduction through the Schottky barrier

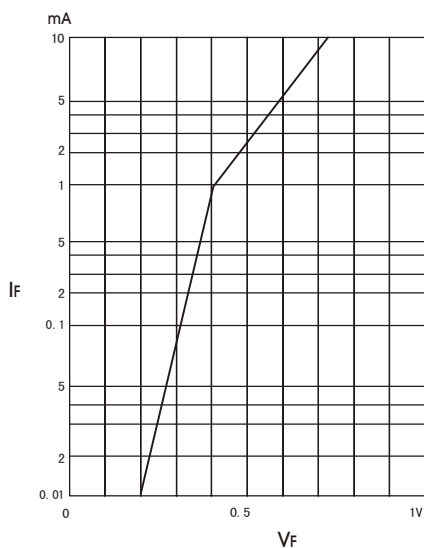


Fig.2 Typical forward conduction curve of combination Schottky barrier and PN junction guard ring

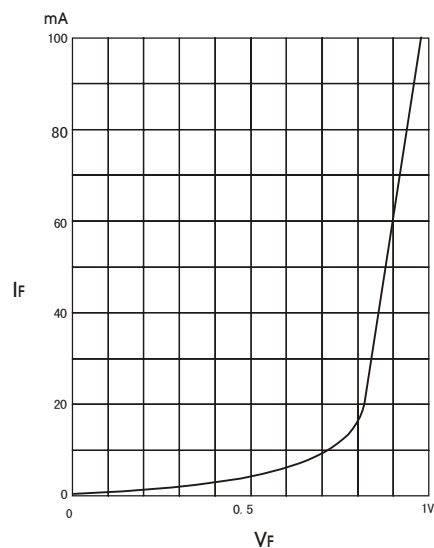


Fig.3 Typical variation of reverse current at various temperatures

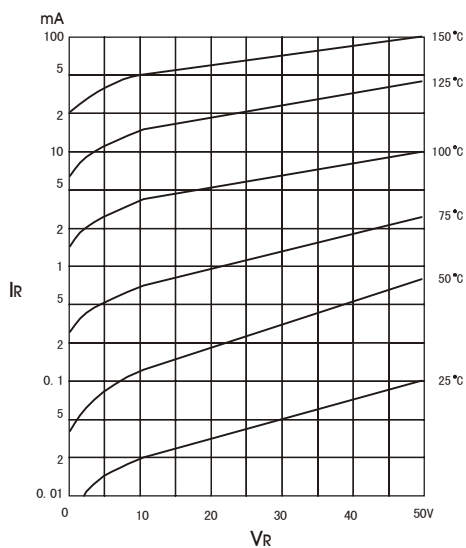


Fig.4 Typical capacitance curve as a function of reverse voltage

